Yiming Li

List of Publications by Year in descending order

346 papers	3,360 citations	218677 26 h-index	289244 40 g-index
348 all docs	348 docs citations	348 times ranked	1592 citing authors

#	Article	IF	Citations
1	Gateâ€allâ€around nanowire vertical tunneling FETs by ferroelectric internal voltage amplification. Nanotechnology, 2022, 33, 055201.	2.6	10
2	Gateway towards recent developments in quantum dot-based light-emitting diodes. Nanoscale, 2022, 14, 4042-4064.	5.6	14
3	Significance of Work Function Fluctuations in SiGe/Si Hetero-Nanosheet Tunnel-FET at Sub-3 nm Nodes. IEEE Transactions on Electron Devices, 2022, 69, 434-438.	3.0	14
4	First Demonstration of Heterogeneous IGZO/Si CFET Monolithic 3-D Integration With Dual Work Function Gate for Ultralow-Power SRAM and RF Applications. IEEE Transactions on Electron Devices, 2022, 69, 2101-2107.	3.0	9
5	Effects of Random Nanosized TiN Grain on Characteristic of Gate-All-Around FinFETs with Ferroelectric HZO Layer. Nanoscale Research Letters, 2022, 17, 16.	5.7	2
6	Room-temperature and high-quality HfO2/SiO2 gate stacked film grown by neutral beam enhanced atomic layer deposition. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2022, 40, .	2.1	7
7	A 0.6-dB Low Loss and 3â€“165 GHz Wideband Phase Difference Sub-THz Coupler in 0.18-Î¼m CMOS. IEEE Microwave and Wireless Components Letters, 2022, 32, 531-534.	3.2	0
8	Device-Simulation-Based Machine Learning Technique for the Characteristic of Line Tunnel Field-Effect Transistors. IEEE Access, 2022, 10, 53098-53107.	4.2	2
9	A Nanosized-Metal-Grain Pattern-Dependent Model for Work-Function Fluctuation of Gate-All-Around Silicon Nanofin and Nanosheet MOSFETs. , 2022, , .		1
10	Deep Learning Approach to Modeling and Exploring Random Sources of Gate-All-Around Silicon Nanosheet MOSFETs. , 2022, , .		3
11	Design of GAA Nanosheet Ferroelectric Area Tunneling FET and Its Significance with DC/RF Characteristics Including Linearity Analyses. Nanoscale Research Letters, 2022, 17, 53.	5.7	8
12	DC Characteristics and Dynamic Properties of Multi-Channel Nanosheet MOSFETs with and without Tungsten Metal Sidewall for Sub-3-nm Technological Nodes. ECS Journal of Solid State Science and Technology, 2022, 11, 065001.	1.8	2
13	Deep Learning Approach to Estimating Work Function Fluctuation of Gate-All-Around Silicon Nanosheet MOSFETs with A Ferroelectric HZO Layer. , 2022, , .		1
14	Investigation on Polarization and Trapping Dominated Reliability for Ferroelectric-HfZrO_x Ge FinFET Inverters. , 2022, , .		1
15	A Machine Learning Approach to Modeling Intrinsic Parameter Fluctuation of Gate-All-Around Si Nanosheet MOSFETs. IEEE Access, 2022, 10, 71356-71369.	4.2	7
16	Machine Learning Approach to Characteristic Fluctuation of Bulk FinFETs Induced by Random Interface Traps. , 2022, , .		3
17	A Unified Statistical Analysis of Comprehensive Fluctuations of Gate-All-Around Silicon Nanosheet MOSFETs Induced by RDF, ITF, and WKF Simultaneously. , 2022, , .		4
18	Model Auto Extraction for Gate-All-Around Silicon Nanowire MOSFETs Using A Decomposition-Based Many-Objective Evolutionary Algorithm. , 2022, , .		0

#	Article	IF	Citations
19	High Electron Mobility Germanium FinFET Fabricated by Atomic Layer Defect-Free and Roughness-Free Etching. IEEE Open Journal of Nanotechnology, 2021, 2, 26-30.	2.0	8
20	Deep Learning Approach to Inverse Grain Pattern of Nanosized Metal Gate for Multichannel Gate-All-Around Silicon Nanosheet MOSFETs. IEEE Transactions on Semiconductor Manufacturing, 2021, 34, 513-520.	1.7	18
21	On the energy band of neutral-beam etched Si/Si0.7Ge0.3 nanopillars. Japanese Journal of Applied Physics, 2021, 60, SBBI03.	1.5	1
22	Surface wettability of silicon nanopillar array structures fabricated by biotemplate ultimate top-down processes. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2021, 39, 023202.	2.1	1
23	Machine Learning Approach to Predicting Tunnel Field-Effect Transistors. , 2021, , .		3
24	p-SiGe nanosheet line tunnel field-effect transistors with ample exploitation of ferroelectric. Japanese Journal of Applied Physics, 2021, 60, 054001.	1.5	7
25	A Novel Design of Ferroelectric Nanowire Tunnel Field Effect Transistors. , 2021, , .		1
26	Characteristics of Stacked Gate-All-Around Si Nanosheet MOSFETs With Metal Sidewall Source/Drain and Their Impacts on CMOS Circuit Properties. IEEE Transactions on Electron Devices, 2021, 68, 3124-3128.	3.0	33
27	Increase in the Efficiency of III-Nitride Micro-LEDs: Atomic-Layer Deposition and Etching. IEEE Nanotechnology Magazine, 2021, 15, 18-34.	1.3	14
28	Si Nanopillar/SiGe Composite Structure for Thermally Managed Nano-devices. , 2021, , .		2
29	Promised Design of Energy-Efficient Negative-Capacitance Vertical Tunneling FET. ECS Journal of Solid State Science and Technology, 2021, 10, 075002.	1.8	8
30	Work-Function Fluctuation of Gate-All-Around Silicon Nanowire n-MOSFETs: A Unified Comparison Between Cuboid and Voronoi Methods. IEEE Journal of the Electron Devices Society, 2021, 9, 151-159.	2.1	14
31	Machine Learning Aided Device Simulation of Work Function Fluctuation for Multichannel Gate-All-Around Silicon Nanosheet MOSFETs. IEEE Transactions on Electron Devices, 2021, 68, 5490-5497.	3.0	21
32	Deep Learning Algorithms for the Work Function Fluctuation of Random Nanosized Metal Grains on Gate-All-Around Silicon Nanowire MOSFETs. IEEE Access, 2021, 9, 73467-73481.	4.2	18
33	Management of Phonon Transport in Lateral Direction for Gap-Controlled Si Nanopillar/SiGe Interlayer Composite Materials. IEEE Open Journal of Nanotechnology, 2021, 2, 148-152.	2.0	2
34	A Nanosized-Metal-Grain Pattern-Dependent Threshold Voltage Model for the Work Function Fluctuation of GAA Si NW MOSFETs. IEEE Access, 2021, 9, 168613-168623.	4.2	2
35	Low resistive InGaN film grown by metalorganic chemical vapor deposition. Vacuum, 2020, 171, 108974.	3.5	7
36	Random telegraph noise in gate-all-around silicon nanowire MOSFETs induced by a single charge trap or random interface traps. Journal of Computational Electronics, 2020, 19, 253-262.	2.5	14

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37	Effects of a dual spacer on electrical characteristics and random telegraph noise of gate-all-around silicon nanowire p-type metalâ€“oxideâ€“semiconductor field-effect transistors. Japanese Journal of Applied Physics, 2020, 59, SGGA02.	1.5	7
38	High Performance GaN HEMT and Ge Fin FET Device Realizing by Atomic-layer Defect-free Etching with Chlorine Neutral Beam. , 2020, , .		0
39	Fabrication and simulation of neutral-beam-etched silicon nanopillars. Vacuum, 2020, 181, 109577.	3.5	5
40	Scaling Limitations of Line TFETs at Sub-8-nm Technology Node. , 2020, , .		5
41	Circuit-Simulation-Based Design Optimization of 3.5 GHz Doherty Power Amplifier via Multi-Objective Evolutionary Algorithm and Unified Optimization Framework. , 2020, , .		3
42	Effects of Spacer and Single-Charge Trap on Voltage Transfer Characteristics of Gate-All-Around Silicon Nanowire CMOS Devices and Circuits. , 2020, , .		11
43	Effects of random number and location of the nanosized metal grains on the threshold voltage variability of silicon gate-all-around nanowire n-type metal-oxide-semiconductor field-effect transistors. Journal of Computational Electronics, 2020, 19, 1478-1484.	2.5	6
44	New Proficient Ferroelectric Nanosheet Line Tunneling FETs with Strained SiGe through Scaled n-epitaxial Layer. , 2020, , .		5
45	Design and Simulation of High Performance Lattice Matched Double Barrier Normally Off AlInGaN/GaN HEMTs. IEEE Journal of the Electron Devices Society, 2020, 8, 873-878.	2.1	10
46	Statistical Prediction of Nanosized-Metal-Grain-Induced Threshold-Voltage Variability for 3D Vertically Stacked Silicon Gate-All-Around Nanowire n-MOSFETs. Journal of Electronic Materials, 2020, 49, 6865-6871.	2.2	3
47	Influence of Fringing-Field on DC/AC Characteristics of Siâ‚‹â€“Geâ€“ Based Multi-Channel Tunnel FETs. IEEE Access, 2020, 8, 208658-208668.	4.2	16
48	Numerical Simulation of Thermal Conductivity of SiNWâ€“SiGe0.3 Composite for Thermoelectric Applications. IEEE Transactions on Electron Devices, 2020, 67, 2088-2092.	3.0	3
49	Optimal Inter-Gate Separation and Overlapped Source of Multi-Channel Line Tunnel FETs. IEEE Open Journal of Nanotechnology, 2020, 1, 38-46.	2.0	16
50	Highly Water-Repellent Nanostructure on Quartz Surface Based on Cassie-Baxter Model With Filling Factor. IEEE Open Journal of Nanotechnology, 2020, 1, 1-5.	2.0	1
51	High-Performance Metal-Ferroeletric-Semiconductor Nanosheet Line Tunneling Field Effect Transistors with Strained SiGe. , 2020, , .		6
52	Energy Band Calculation of Si/Si0.7 Ge0.3 Nanopillars in kâž™ Space. , 2020, , .		0
53	Automatic Device Model Parameter Extractions via Hybrid Intelligent Methodology. , 2020, , .		2
54	Atomic layer defect-free etching for germanium using HBr neutral beam. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2019, 37, 051001.	2.1	4

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55	Barrier Engineering of Lattice Matched AlInGaN/ GaN Heterostructure Toward High Performance E-mode Operation. , 2019, , .		1
56	Variability of Threshold Voltage Induced by Work-Function Fluctuation and Random Dopant Fluctuation on Gate-All-Around Nanowire nMOSFETs. , 2019, , .		1
57	Atomic layer germanium etching for 3D Fin-FET using chlorine neutral beam. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2019, 37, .	2.1	15
58	Characteristic Fluctuations of Dynamic Power Delay Induced by Random Nanosized Titanium Nitride Grains and the Aspect Ratio Effect of Gate-All-Around Nanowire CMOS Devices and Circuits. Materials, 2019, 12, 1492.	2.9	6
59	Random Nanosized Metal Grains and Interface-Trap Fluctuations in Emerging CMOS Technologies. , 2019, , 123-134.		3
60	Contact Engineering of Trilayer Black Phosphorus With Scandium and Gold. IEEE Journal of the Electron Devices Society, 2019, 7, 322-328.	2.1	2
61	Electrical Characteristic of AlGaN/GaN High-Electron-Mobility Transistors With Recess Gate Structure. IEEE Transactions on Electron Devices, 2019, 66, 1694-1698.	3.0	31
62	Impact of Doping Concentration on Electronic Properties of Transition Metal-Doped Monolayer Molybdenum Disulfide. IEEE Transactions on Electron Devices, 2018, 65, 733-738.	3.0	17
63	DC/AC/RF Characteristic Fluctuations Induced by Various Random Discrete Dopants of Gate-All-Around Silicon Nanowire n-MOSFETs. IEEE Transactions on Electron Devices, 2018, 65, 2638-2646.	3.0	23
64	Analysis of In-Line Process Parameters of the Unity Gain Frequency of HKMG Bulk FinFET Devices. IEEE Electron Device Letters, 2018, 39, 335-338.	3.9	5
65	Effect of ALD-Al2O3 Passivated Silicon Quantum Dot Superlattices on p/i/n+ Solar Cells. IEEE Transactions on Electron Devices, 2017, 64, 2886-2892.	3.0	4
66	Impacts of plasma-induced damage due to UV light irradiation during etching on Ge fin fabrication and device performance of Ge fin field-effect transistors. Applied Physics Express, 2017, 10, 026501.	2.4	33
67	Physical and electrical characteristics of Si/SiC quantum dot superlattice solar cells with passivation layer of aluminum oxide. Nanotechnology, 2017, 28, 485401.	2.6	0
68	Design and Simulation of Intermediate Band Solar Cell With Ultradense Type-II Multilayer Ge/Si Quantum Dot Superlattice. IEEE Transactions on Electron Devices, 2017, 64, 4547-4553.	3.0	7
69	Design and simulation of Si/SiC quantum dot superlattice solar cells with Al<inf>2</inf>O<inf>3</inf> passivation layer. , 2017, , .		0
70	On electronic structure and geometry of MoX<inf>2</inf> (X = S, Se, Te) and black phosphorus by ab initio Simulation with various van der waals corrections. , 2017, , .		4
71	Asymmetric characteristic fluctuation of undoped gate-all-around nanowire MOSFETs induced by random discrete dopants inside source/drain extensions. , 2017, , .		2
72	Impact of silicon quantum dot super lattice and quantum well structure as intermediate layer on pâ€iâ€n silicon solar cells. Progress in Photovoltaics: Research and Applications, 2016, 24, 774-780.	8.1	20

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73	A Systematic Approach to Correlation Analysis of In-Line Process Parameters for Process Variation Effect on Electrical Characteristic of 16-nm HKMG Bulk FinFET Devices. IEEE Transactions on Semiconductor Manufacturing, 2016, 29, 209-216.	1.7	7
74	Statistical device simulation of characteristic fluctuation of 10-nm gate-all-around silicon nanowire MOSFETs induced by various discrete random dopants. , 2016, , .		4
75	Miniband formulation of bilayer type II Ge/Si quantum dot superlattices. , 2016, , .		1
76	Simulation Study of Multilayer Si/SiC Quantum Dot Superlattice for Solar Cell Applications. IEEE Electron Device Letters, 2016, , 1-1.	3.9	6
77	Suspended Diamond-Shaped Nanowire With Four {111} Facets for High-Performance Ge Gate-All-Around FETs. IEEE Transactions on Electron Devices, 2016, 63, 3837-3843.	3.0	5
78	Process-Dependence Analysis for Characteristic Improvement of Ring Oscillator Using 16-nm Bulk FinFET Devices. IEEE Transactions on Electron Devices, 2016, , 1-6.	3.0	4
79	Miniband formulation in Ge/Si quantum dot array. Japanese Journal of Applied Physics, 2016, 55, 04EJ14.	1.5	6
80	A Novel Driving Method for High-Performance Amorphous Silicon Gate Driver Circuits in Flat Panel Display Industry. Journal of Display Technology, 2016, 12, 1051-1056.	1.2	8
81	Step buffer layer of Al_{0.25}Ga_{0.75}N/Al_{0.08}Ga_{0.92}N on P-InAlN gate normally-off high electron mobility transistors. Semiconductor Science and Technology, 2016, 31, 075006.	2.0	11
82	Optimal design of a novel amorphous silicon gate driver circuit using a TFT-circuit-simulation-based multi-objective evolutionary algorithm. Journal of Information Display, 2016, 17, 51-58.	4.0	2
83	Optimal Geometry Aspect Ratio of Ellipse-Shaped-Surrounding-Gate Nanowire Field Effect Transistors. Journal of Nanoscience and Nanotechnology, 2016, 16, 920-923.	0.9	1
84	Optimal design of the multiple-apertures-GaN-based vertical HEMTs with $$hbox {SiO}_{2}$$ SiO 2 current blocking layer. Journal of Computational Electronics, 2016, 15, 154-162.	2.5	12
85	32-nm Multigate Si-nTFET With Microwave-Annealed Abrupt Junction. IEEE Transactions on Electron Devices, 2016, 63, 1808-1813.	3.0	8
86	Tuning of the electron<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mi>g</mml:mi></mml:math>factor in defect-free GaAs nanodisks. Physical Review B, 2015, 92, .	3.2	5
87	Simulation study of 14-nm-gate III-V trigate field effect transistor devices with In1â^'xGaxAs channel capping layer. AIP Advances, 2015, 5, 067107.	1.3	0
88	Diamond-shaped Ge and Ge0.9Si0.1 gate-all-around nanowire FETs with four {111} facets by dry etch technology. , 2015, , .		17
89	Process variation effect, metal-gate work-function fluctuation and random dopant fluctuation of 10-nm gate-all-around silicon nanowire MOSFET devices. , 2015, , .		47
90	Optimal Channel Doping Profile of Two-Dimensional Metal-Oxide-Semiconductor Field-Effect Transistors via Geometric Programming. Journal of Advanced Simulation in Science and Engineering, 2015, 2, 178-200.	0.2	0

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91	Electrical characteristic and power consumption fluctuations of trapezoidal bulk FinFET devices and circuits induced by random line edge roughness. , 2015, , .		5
92	Electrical characteristic fluctuation of 16-nm-gate trapezoidal bulk FinFET devices with fixed top-fin width induced by random discrete dopants. Nanoscale Research Letters, 2015, 10, 116.	5.7	19
93	Determination of Source-and-Drain Series Resistance in 16-nm-Gate FinFET Devices. IEEE Transactions on Electron Devices, 2015, 62, 1663-1667.	3.0	10
94	Source/Drain Series Resistance Extraction in HKMG Multifin Bulk FinFET Devices. IEEE Transactions on Semiconductor Manufacturing, 2015, 28, 193-199.	1.7	9
95	Circuit-Simulation-Based Multi-Objective Evolutionary Algorithm for Design Optimization of a-Si:H TFTs Gate Driver Circuits Under Multilevel Clock Driving. Journal of Display Technology, 2015, 11, 640-645.	1.2	3
96	Design, Fabrication and Characterization of Low-Noise and High-Reliability Amorphous Silicon Gate Driver Circuit for Advanced FPD Applications. Journal of Display Technology, 2015, 11, 633-639.	1.2	1
97	Capacitance Characteristic Optimization of Germanium MOSFETs with Aluminum Oxide by Using a Semiconductor-Device-Simulation-Based Multi-Objective Evolutionary Algorithm Method. Materials and Manufacturing Processes, 2015, 30, 520-528.	4.7	6
98	Miniband Calculation of 3-D Nanostructure Array for Solar Cell Applications. IEEE Transactions on Electron Devices, 2015, 62, 3709-3714.	3.0	17
99	Electronic structure dependence on the density, size and shape of Ge/Si quantum dots array. , 2015, , .		1
100	A novel AlGaN/GaN multiple aperture vertical high electron mobility transistor with silicon oxide current blocking layer. Vacuum, 2015, 118, 59-63.	3.5	20
101	High-reliability and low-noise amorphous-silicon gate with a novel clock-driving methodology. Journal of Information Display, 2014, 15, 5-11.	4.0	4
102	The impact of fin/sidewall/gate line edge roughness on trapezoidal bulk FinFET devices. , 2014, , .		7
103	Electrical characteristic fluctuation of 16-nm-gate high-Î²/metal gate bulk FinFET devices in the presence of random interface traps. Nanoscale Research Letters, 2014, 9, 633.	5.7	8
104	Design optimization of 16-nm bulk FinFET technology via geometric programming. , 2014, , .		2
105	Random-work-function-induced characteristic fluctuation in 16-nm-gate bulk and SOI FinFETs. International Journal of Nanotechnology, 2014, 11, 1029.	0.2	4
106	Simulation study on electrical characteristic of AlGaN/GaN high electron mobility transistors with AlN spacer layer. Japanese Journal of Applied Physics, 2014, 53, 04EF08.	1.5	34
107	On characteristic fluctuation of nonideal bulk FinFET devices. , 2014, , .		0
108	Realistic quantum design of silicon quantum dot intermediate band solar cells. Nanotechnology, 2013, 24, 265401.	2.6	14

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109	Computer simulation of electron energy state spin-splitting in nanoscale InAs/GaAs semiconductor quantum rings. Mathematical and Computer Modelling, 2013, 58, 300-305.	2.0	1
110	Mobility model extraction for surface roughness of SiGe along (110) and (100) Orientations in HKMG bulk FinFET devices. Microelectronic Engineering, 2013, 109, 357-359.	2.4	11
111	Multiobjective evolutionary approach to silicon solar cell design optimization. , 2013, , .		3
112	Statistical device simulation of intrinsic parameter fluctuation in 16-nm-gate n- and p-type Bulk FinFETs. , 2013, , .		0
113	Type-II Ge/Si quantum dot superlattice for intermediate-band solar cell applications. , 2013, , .		1
114	Modeling miniband for realistic silicon nanocrystal array. Mathematical and Computer Modelling, 2013, 58, 306-311.	2.0	8
115	The intrinsic parameter fluctuation on high-Î²/metal gate bulk FinFET devices. Microelectronic Engineering, 2013, 109, 302-305.	2.4	7
116	Geometric programming approach to doping profile design optimization of metal-oxide-semiconductor devices. Mathematical and Computer Modelling, 2013, 58, 344-354.	2.0	9
117	Device Simulationâ€“Based Multiobjective Evolutionary Algorithm for Process Optimization of Semiconductor Solar Cells. Materials and Manufacturing Processes, 2013, 28, 761-767.	4.7	6
118	Simulation study of type-II Ge/Si quantum dot for solar cell applications. Journal of Applied Physics, 2013, 114, 124509.	2.5	23
119	Optimal power consumption design of the amorphous silicon thin-film transistor gate driver circuit for 10.1-in. display panel manufacturing. Journal of Information Display, 2013, 14, 13-19.	4.0	6
120	On characteristic variability of 16-nm-gate bulk FinFET devices induced by intrinsic parameter fluctuation and process variation effect. , 2013, , .		4
121	Characteristic and Fluctuation of Multi-fin FinFETs. Lecture Notes in Nanoscale Science and Technology, 2013, , 125-158.	0.8	0
122	Random Interface-Traps-Induced Electrical Characteristic Fluctuation in 16-nm-Gate High-$kappa$/Metal Gate Complementary Metalâ€“Oxideâ€“Semiconductor Device and Inverter Circuit. Japanese Journal of Applied Physics, 2012, 51, 04DC08.	1.5	2
123	Toward full fluctuation analysis of small FETs. , 2012, , .		4
124	kâ‹…p WURTZITE HAMILTONIAN AND OPTICAL MATRIX WITH BULK INVERSION ASYMMETRY. Modern Physics Letters B, 2012, 26, 1150002.	1.9	0
125	Threshold Voltage Fluctuation in 16-nm-Gate FinFETs Induced by Random Work Function of Nanosized Metal Grain. Journal of Nanoscience and Nanotechnology, 2012, 12, 4485-4488.	0.9	4
126	50% Efficiency intermediate band solar cell design using highly periodical silicon nanodisk array. , 2012, , .		4

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127	Multi-objective Display Panel Design Optimization Using Circuit Simulation-Based Evolutionary Algorithm. , 2012, , .		0
128	Statistical device simulation of physical and electrical characteristic fluctuations in 16-nm-gate high-Î¹/metal gate MOSFETs in the presence of random discrete dopants and random interface traps. Solid-State Electronics, 2012, 77, 12-19.	1.4	7
129	Velocity-direction dependent transmission coefficient of electron through potential barrier grown on anisotropic semiconductor. Semiconductors, 2012, 46, 1126-1134.	0.5	0
130	In-plane miniband formation of Si Nanodisc and its application in intermediate band photovoltaic. , 2012, , .		1
131	Application of block diagonal technique to a Hamiltonian matrix in performing spin-splitting calculations for GaN wurtzite materials. Journal of the Korean Physical Society, 2012, 60, 403-409.	0.7	0
132	3D simulation of morphological effect on reflectance of Si3N4 sub-wavelength structures for silicon solar cells. Nanoscale Research Letters, 2012, 7, 196.	5.7	6
133	Random Interface-Traps-Induced Electrical Characteristic Fluctuation in 16-nm-Gate High-Î¹/Metal Gate Complementary Metalâ€“Oxideâ€“Semiconductor Device and Inverter Circuit. Japanese Journal of Applied Physics, 2012, 51, 04DC08.	1.5	4
134	A unified 3D device simulation of random dopant, interface trap and work function fluctuations on high-к/metal gate device. , 2011, , .		19
135	Modeling temperature and bias stress effects on threshold voltage of a-Si:H TFTs for gate driver circuit simulation. , 2011, , .		3
136	Random work functions induced DC and dynamic characteristic fluctuations in 16-nm high-κ/metal gate CMOS device and digital circuit. , 2011, , .		3
137	3D finite element simulation of morphological effect on reflectance of Si<inf>3</inf>N<inf>4</inf> sub-wavelength structures for silicon solar cells. , 2011, , .		0
138	Correlation between interface traps and random dopants in emerging MOSFETs. , 2011, , .		2
139	Modelling competition in global LCD TV industry. Applied Economics, 2011, 43, 2969-2981.	2.2	8
140	Hybrid Differential Evolution and Particle Swarm Optimization Approach to Surface-Potential-Based Model Parameter Extraction for Nanoscale MOSFETs. Materials and Manufacturing Processes, 2011, 26, 388-397.	4.7	10
141	Large-scale statistical simulation of characteristic variation in 16-nm-gate Bulk FinFET devices due to work function fluctuation. , 2011, , .		0
142	Dynamic Characteristic Optimization of 14 a-Si:H TFTs Gate Driver Circuit Using Evolutionary Methodology for Display Panel Manufacturing. Journal of Display Technology, 2011, 7, 274-280.	1.2	13
143	Surface-Enhanced Raman Scattering Active Substrates. IEEE Nanotechnology Magazine, 2011, 5, 12-16.	1.3	1
144	Investigation of Raman enhancement in hydrothermally roughened SERS-active substrates. Computer Physics Communications, 2011, 182, 260-262.	7.5	1

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145	Quantum hydrodynamic simulation of discrete-dopant fluctuated physical quantities in nanoscale FinFET. Computer Physics Communications, 2011, 182, 96-98.	7.5	9
146	Interface traps and random dopants induced characteristic fluctuations in emerging MOSFETs. Microelectronic Engineering, 2011, 88, 1269-1271.	2.4	7
147	Nanosized metal grains induced electrical characteristic fluctuation in 16-nm-gate high-Î¤/metal gate bulk FinFET devices. Microelectronic Engineering, 2011, 88, 1240-1242.	2.4	18
148	Nanosized-Metal-Grain-Induced Characteristic Fluctuation in 16 nm Complementary Metalâ€“Oxideâ€“Semiconductor Devices and Digital Circuits. Japanese Journal of Applied Physics, 2011, 50, 04DC22.	1.5	6
149	Nanosized metal grains induced electrical characteristic fluctuation in 16 nm bulk and SOI FinFET devices with TiN/HfO<inf>2</inf> gate stack. , 2011, , .		1
150	A novel integrated amorphous silicon TFT gate driver circuit with optimized design for TFT-LCD display panel manufacturing. , 2011, , .		2
151	Local field enhancement dependence on nanoparticle's geometry in Au/TiO<inf>2</inf>/Ti/Si SERS-active substrate for biochemical sensors. , 2011, , .		0
152	Random interface-traps-induced characteristic fluctuation in 16-nm high-к/metal gate CMOS device and SRAM circuit. , 2011, , .		2
153	Dual-Material Gate Approach to Suppression of Random-Dopant-Induced Characteristic Fluctuation in 16 nm Metalâ€“Oxideâ€“Semiconductor Field-Effect-Transistor Devices. Japanese Journal of Applied Physics, 2011, 50, 04DC07.	1.5	3
154	Dual-Material Gate Approach to Suppression of Random-Dopant-Induced Characteristic Fluctuation in 16 nm Metalâ€“Oxideâ€“Semiconductor Field-Effect-Transistor Devices. Japanese Journal of Applied Physics, 2011, 50, 04DC07.	1.5	2
155	Nanosized-Metal-Grain-Induced Characteristic Fluctuation in 16 nm Complementary Metalâ€“Oxideâ€“Semiconductor Devices and Digital Circuits. Japanese Journal of Applied Physics, 2011, 50, 04DC22.	1.5	1
156	kÂ·p Zincblende Hamiltonian and Optical Matrix with Bulk Inversion Asymmetry. Japanese Journal of Applied Physics, 2011, 50, 081202.	1.5	0
157	Process-Variation Effect, Metal-Gate Work-Function Fluctuation, and Random-Dopant Fluctuation in Emerging CMOS Technologies. IEEE Transactions on Electron Devices, 2010, 57, 437-447.	3.0	110
158	Shape Effect of Silicon Nitride Subwavelength Structure on Reflectance for Silicon Solar Cells. IEEE Transactions on Electron Devices, 2010, 57, 2427-2433.	3.0	30
159	Novel Metamorphic HEMTs With Highly Doped InGaAs Source/Drain Regions for High Frequency Applications. IEEE Transactions on Electron Devices, 2010, 57, 2594-2598.	3.0	13
160	The impact of high-frequency characteristics induced by intrinsic parameter fluctuations in nano-MOSFET device and circuit. Microelectronics Reliability, 2010, 50, 657-661.	1.7	10
161	Simulation-based evolutionary method in antenna design optimization. Mathematical and Computer Modelling, 2010, 51, 944-955.	2.0	14
162	Temperature-aware floorplanning via geometric programming. Mathematical and Computer Modelling, 2010, 51, 927-934.	2.0	11

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163	Optimization on configuration of surface conduction electron-emitters. Microelectronics Reliability, 2010, 50, 699-703.	1.7	6
164	Device and circuit level suppression techniques for random-dopant-induced static noise margin fluctuation in 16-nm-gate SRAM cell. Microelectronics Reliability, 2010, 50, 647-651.	1.7	2
165	Statistical variability in FinFET devices with intrinsic parameter fluctuations. Microelectronics Reliability, 2010, 50, 635-638.	1.7	12
166	Forecasting global adoption of crystal display televisions with modified product diffusion model. Computers and Industrial Engineering, 2010, 58, 553-562.	6.3	24
167	Statistical simulation of metal-gate work-function fluctuation in high-κ/metal-gate devices. , 2010, , .		5
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